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THE FOLLOWING IS THE ENGLISH TRANSLATION OF THE
ANNEXES TO THE INTERNATIONAL PRELIMINARY
EXAMINATION REPORT : AMENDED SHEETS (Pages 52, 53 and 54)
FILED ON 12-11-00.

Amendment under article 34

filed on December 11, 2000

CLAIMS

1. (Cancelled)

5 2. (Cancelled)

3. (Cancelled)

4. A carbon-containing aluminum nitride sintered body
10 comprising both of:

Al carbon whose peak cannot be detected on its X-ray
diffraction chart or whose peak is below its detection limit
thereon; and

15 carbon whose peak can be detected thereon,
in a matrix made of aluminum nitride.

5. The carbon-containing aluminum nitride sintered body
according to claim 4,

wherein:

20 said carbon whose peak cannot be detected on its X-ray
diffraction chart or whose peak is below its detection limit
thereon, is at least one of amorphous carbon, and carbon forming
solid solution in the phase of aluminum nitride crystal; and

25 said carbon whose peak can be detected thereon is
crystalline carbon.

6. The carbon-containing aluminum nitride sintered body
according to claim 4 or 5,

Sub C2) which comprises both of crystalline carbon and amorphous
30 carbon.

7. The carbon-containing aluminum nitride sintered body
according to any of claims 4 to 6,

35 which comprises said carbon in a total amount of 200 to
5000 ppm.

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8. (Cancelled)

Sub C3)
A2 5 9. (Amended) The carbon-containing aluminum nitride sintered body according to any of claims 4 to 7, wherein its brightness defined in JIS Z 8721 is N4 or less.

10. (Cancelled)

10 11. (Cancelled)

12. (Cancelled)

A3 15 13. A ceramic substrate for a semiconductor-producing/examining device, wherein a ceramic substrate: comprising both of: carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon; and
20 carbon whose peak can be detected thereon, is provided with a conductor.

25 14. The ceramic substrate for the semiconductor-producing/examining device according to claim 13,

wherein:

30 said carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon, is at least one of amorphous carbon, and carbon forming solid solution in the phase of aluminum nitride crystal; and
said carbon whose peak can be detected thereon is crystalline carbon.

Sub C4)
35 15. The ceramic substrate for the semiconductor-producing/examining device according to claim 13

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or 14,

wherein the content of said carbon is from 200 to 5000 ppm.

5 16. (Cancelled)

17. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 9, and 13 to 15,

10 wherein its brightness defined in JIS Z 8721 is N4 or less.

18. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 9, 13 to 15, and 17,

15 wherein:

said conductor is an electrostatic electrode; and
said ceramic substrate functions as an electrostatic chuck.

19. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 9, 13 to 15, and 17,

wherein:

said conductor is a resistance heating element; and
25 said ceramic substrate functions as a hot plate.

20. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 9, 13 to 15, and 17,

30 wherein:

said conductor is formed: on a surface of the ceramic substrate; and inside the ceramic substrate;

said inside conductor is at least one of a guard electrode and a ground electrode; and

35 said ceramic substrate functions as a wafer prober.

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filed on January 24, 2001

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or 14,

wherein the content of said carbon is from 200 to 5000 ppm.

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5 16. (Cancelled)

17. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 13 to 15,

10 wherein its brightness defined in JIS Z 8721 is N4 or less.

18. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 13 to 15, and 17,

15 wherein:

said conductor is an electrostatic electrode; and

said ceramic substrate functions as an electrostatic chuck.

19. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 13 to 15, and 17,

wherein:

said conductor is a resistance heating element; and

25 said ceramic substrate functions as a hot plate.

20. (Amended) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 13 to 15, and 17,

30 wherein:

said conductor is formed: on a surface of the ceramic substrate; and inside the ceramic substrate;

said inside conductor is at least one of a guard electrode and a ground electrode; and

35 said ceramic substrate functions as a wafer prober.

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sub C5)

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21. (Added) A carbon-containing aluminum nitride sintered body according to any of claims 4 to 7,

wherein:

5 said matrix contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,

its brightness defined in JIS Z 8721 is N4 or less.

10 22. (Added) The ceramic substrate for the semiconductor-producing/examining device according to any of claims 13 to 15,

wherein:

15 said ceramic substrate contains a sintering aid comprising at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide; and,

its brightness defined in JIS Z 8721 is N4 or less.

20 23. (Added) A carbon-containing aluminum nitride sintered body comprising: carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon; in a matrix made of aluminum nitride,

wherein its brightness defined in JIS Z 8721 is N4 or less.

25 24. (Added) The carbon-containing aluminum nitride sintered body according to claim 23,

30 wherein: carbon whose peak cannot be detected on its X-ray diffraction chart or whose peak is below its detection limit thereon, is at least one of amorphous carbon, and carbon forming solid solution in the phase of aluminum nitride crystal.

Sub C6) 25. (Added) The carbon-containing aluminum nitride sintered body according to claim 23 or 24,

35 wherein the content of said carbon is from 200 to 5000 ppm.

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sub (6)

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26. (Added) The carbon-containing aluminum nitride sintered body according to any of claims 23 to 25,
wherein said matrix contains a sintering aid comprising
5 at least one of an alkali metal oxide, an alkali earth metal oxide, and a rare earth oxide.
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ADD (7)